

Vishay Siliconix

N-Channel 100 V (D-S) MOSFET



PRODUCT SUMMARY					
V _{DS} (V)	100				
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10 \text{ V}$	0.0038				
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 7.5 \text{ V}$	0.0046				
Q _g typ. (nC)	76				
I _D (A)	120 ^d				
Configuration	Single				

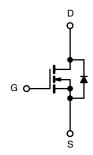
FEATURES

- ThunderFET® power MOSFET
- Maximum 175 °C junction temperature
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



APPLICATIONS

- Power supply
 - Secondary synchronous rectification
- DC/DC converter
- Power tools
- · Motor drive switch
- DC/AC inverter
- · Battery management
- OR-ing



N-Channel MOSFET

ORDERING INFORMATION			
Package	TO-263-7L		
Lead (Pb)-free and halogen-free	SUM70040M-GE3		

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-source voltage		V _{DS}	100	V		
Gate-source voltage		V _{GS}	± 20			
Continuous drain current (T _{.1} = 150 °C)	T _C = 25 °C	I _D	120 ^d	Δ.		
Continuous drain current (1) = 130 C)	T _C = 70 °C	'D	120 ^d			
Pulsed drain current (t = 100 μs)	I _{DM} 480			А		
Avalanche current		I _{AS}	73			
Single avalanche energy ^a	L = 0.1 mH	E _{AS}	266	mJ		
Mayimum nauray discination 2	T _C = 25 °C	P _D	375 b	W		
Maximum power dissipation ^a	T _C = 125 °C	- PD	125 ^b			
Operating junction and storage temperature ran	erating junction and storage temperature range		-55 to +175	°C		

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction-to-ambient (PCB mount) ^c	R _{thJA}	40	°C/W	
Junction-to-case (drain)	R _{thJC}	0.4	- C/W	

Notes

- a. Duty cycle ≤ 1 %
- b. See SOA curve for voltage derating
- c. When mounted on 1" square PCB (FR4 material)
- d. Package limited



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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	100	-	-	V	
Gate threshold voltage	V _{GS(th)}	$V_{DS}=V_{GS},I_D=250\;\mu A$	2.5	-	4	V	
Gate-body leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 250	nA	
		$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	μΑ	
Zero gate voltage drain current	I _{DSS}	V_{DS} = 100 V, V_{GS} = 0 V, T_J = 125 °C	-	-	150		
		V_{DS} = 100 V, V_{GS} = 0 V, T_J = 175 °C	-	-	5	mA	
On-state drain current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	120	-	-	Α	
Drain course on state resistance 3	D	V _{GS} = 10 V, I _D = 20 A	-	0.0030	0.0038		
Drain-source on-state resistance ^a	R _{DS(on)}	$V_{GS} = 7.5 \text{ V}, I_D = 15 \text{ A}$	-	0.0035	0.0046	Ω	
Forward transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 20 A	-	82	-	S	
Dynamic ^b							
Input capacitance	C _{iss}		-	5100	-	pF	
Output capacitance	C _{oss}	V _{GS} = 0 V, V _{DS} = 50 V, f = 1 MHz	-	2025	-		
Reverse transfer capacitance	C_{rss}		-	165	-		
Total gate charge ^c	Q_g		-	76	120	nC	
Gate-source charge ^c	Q _{gs}	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	23	-		
Gate-drain charge ^c	Q_{gd}		-	17	-		
Gate resistance	R_g	f = 1 MHz	0.6	3.3	6.6	Ω	
Turn-on delay time ^c	t _{d(on)}		-	15	30		
Rise time ^c	t _r	$V_{DD} = 50 \text{ V}, R_L = 5 \Omega$	-	22	40	20	
Turn-off delay time ^c	t _{d(off)}	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	55	100	ns	
Fall time ^c	t _f		-	15	30		
Drain-Source Body Diode Ratings a	nd Characteri	stics ^b (T _C = 25 °C)					
Pulsed current (t = 100 μs)	I _{SM}		-	-	480	Α	
Forward voltage ^a	V_{SD}	I _F = 10 A, V _{GS} = 0 V	-	0.8	1.5	V	
Reverse recovery time	t _{rr}		-	94	150	ns	
Peak reverse recovery charge	I _{RM(REC)}	$I_F = 20 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$	-	4.6	10	Α	
Reverse recovery charge	Q _{rr}		-	0.23	0.5	μC	

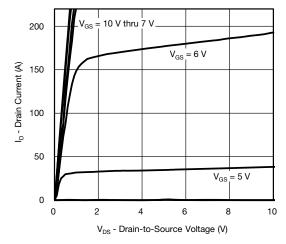
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

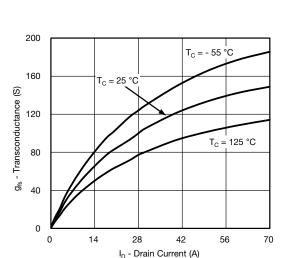
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



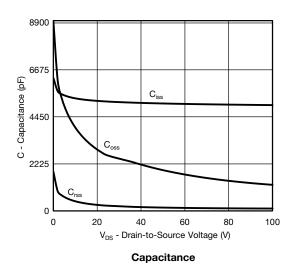
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

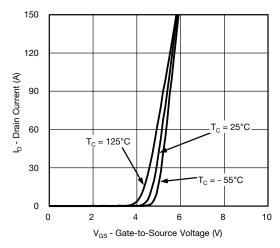


Output Characteristics

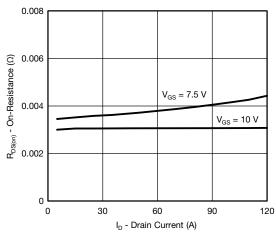


Transconductance

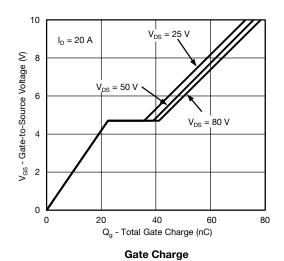




Transfer Characteristics

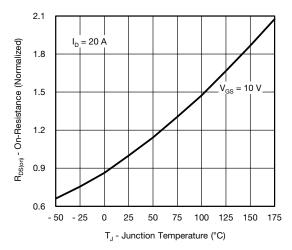


On-Resistance vs. Drain Current

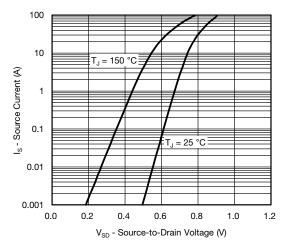




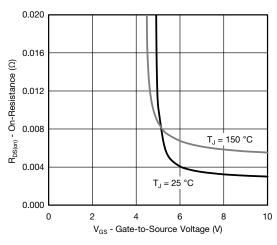
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



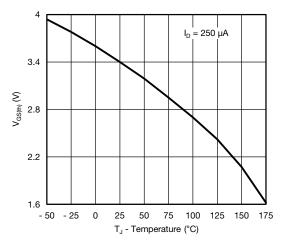
On-Resistance vs. Junction Temperature



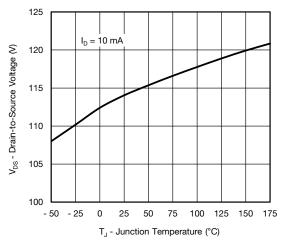
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



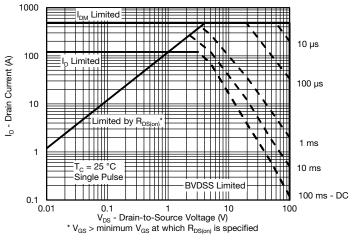
Threshold Voltage



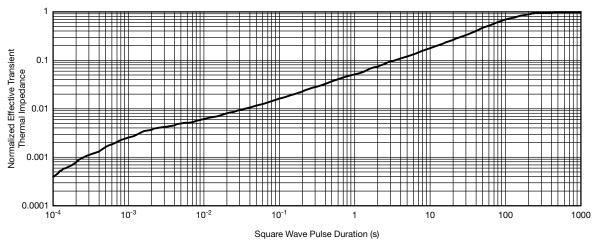
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



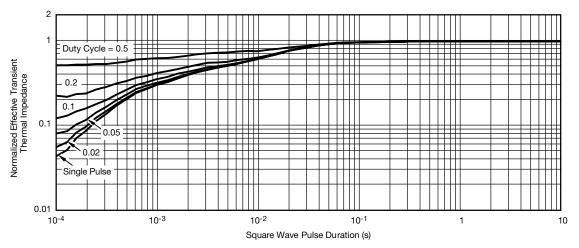
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction to Case (25 °C)

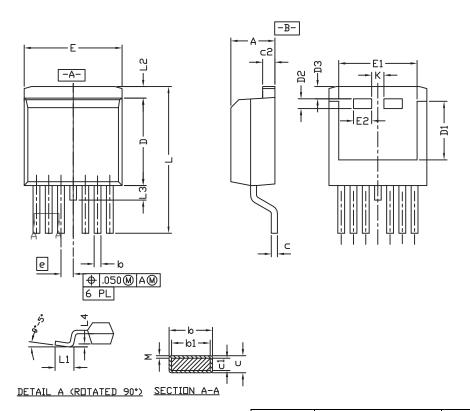
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg265814.





D²PAK (TO-263-7L) Case Outline



Notes

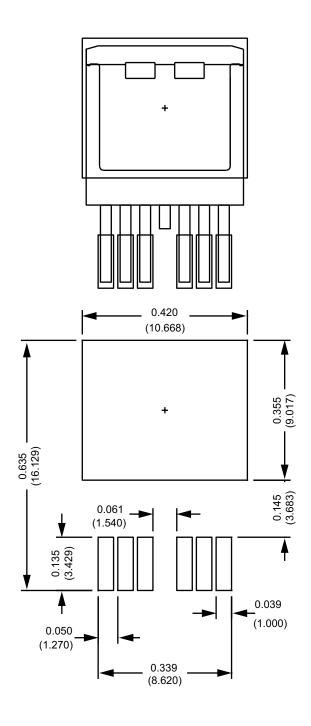
- 1. Plane B includes maximum features of heat sink tab and plastic
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils
- 3. Pin to pin coplanarity max. 4 mils
- 4. Lead thickness 25 mils
- 5. For SUM part numbers lead thickness is 24 mils to 29 mils
- 6. For reference only
- 7. Use inches as the primary measurement
- 8. This feature is only for SUM

	INCHES		MILLIMETERS	
DIM.	MIN.	MAX.	MIN.	MAX.
Α	0.160	0.190	4.064	4.826
b	0.020	0.039	0.508	0.990
b1	0.020	0.035	0.508	0.889
c* SUB	0.012	0.018	0.305	0.457
c* SUM	0.022	0.028	0.559	0.711
c1	0.018	0.025	0.457	0.635
c2	0.045	0.055	1.143	1.397
D	0.340	0.380	8.636	9.652
D1	0.260	0.280	6.604	7.112
D2	0.046	0.050	1.168	1.270
D3	0.045	0.055	1.143	1.397
E	0.380	0.410	9.652	10.414
E1	0.245	-	6.223	-
E2	0.072	0.078	1.829	1.981
е	0.050 BSC		1.27 BSC	
K	0.045	0.055	1.143	1.397
L	0.575	0.625	14.605	15.875
L1	0.090	0.110	2.286	2.794
L2	0.040	0.055	1.016	1.397
L3	0.050	0.070	1.270	1.778
L4	0.010	0.010 BSC		BSC
М	-	0.002	-	0.050
ECN: T22-0410-Rev. D, 19-Sep-2022 DWG: 6006				

Revision: 19-Sep-2022 Document Number: 63782



Recommended Land Pattern D²PAK (TO-263-7L)





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